

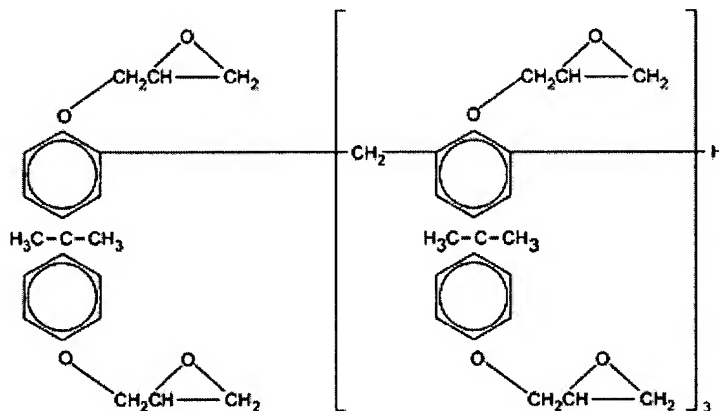
IN THE CLAIMS:

Please amend the claims to read as follows.

1. (currently amended) A photoresist masking material, ~~comprising~~ consisting essentially of:

- a) an octafunctional epoxidized novolac resin;
- b) an organic solvent;
- c) a photopolymerization initiator;
- d) a plasticizer selected from the group consisting of dialkylphthalates, dialkylmalonates, dialkylsebacates, dialkyladipates, and diglycidyl hexahydrophthalates; and
- e) an adhesion promoter selected from the group consisting of glycidoxypropanetrimethoxysilane, mercatopropyltrimethoxysilane, and aminopropyltrimethoxysilane.

2. (original) A photoresist masking material according to claim 1 wherein said octafunctional epoxidized novolac resin is of the formula:



3. (original) A photoresist masking material according to claim 1 wherein said solvent has a boiling point of between 160°C and 260°C.

4. (original) A photoresist masking material according to claim 1 wherein said solvent has a boiling point of between 190°C and 220°C.

5. (original) A photoresist masking material according to claim 1 wherein said solvent has a boiling point of between 200°C and 210°C.

6. (original) A photoresist masking material according to claim 1 wherein said solvent is gamma butyrolactone.

7. (currently amended) A photoresist masking material according to claim 1 wherein said solvent is present in an amount ranging between about 15% and about 45% by weight.

8. (currently amended) A photoresist masking material according to claim 1 wherein said solvent is present in an amount ranging between about 20% and about 30% by weight.

9. (currently amended) A photoresist masking material according to claim 1 wherein said solvent is present in an amount of about 26% by weight.

10. (currently amended) A photoresist masking material according to claim 1 wherein said photopolymerization initiator is present in an amount ranging between about 3% and about 10% by weight.

11. (currently amended) A photoresist masking material according to claim 1 wherein said photopolymerization initiator is present in an amount ranging between about 5% and about 8% by weight.

12. (original) A photoresist masking material according to claim 1 wherein said photopolymerization initiator is present in an amount ranging between about 6% and about 7% by weight.

13. (currently amended) A photoresist masking material according to claim 1 wherein said photopolymerization initiator is ~~Cyrcure[®]-6974~~ a triaryl sulphonium SbF₆ salt.

14. (currently amended) A photoresist masking material according to claim 1 wherein said plasticizer is present in an amount ranging between about 0.5% and about 3% by weight.

15. (currently amended) A photoresist masking material according to claim 1 wherein said plasticizer is present in an amount of about 2% by weight.

16. (currently amended) A photoresist masking material according to claim 1 wherein said plasticizer is a dialkylphthalate by weight.

17. (original) A photoresist masking material according to claim 1 wherein said dialkylphthalate is dioctylphthalate.

18. (currently amended) A photoresist masking material according to claim 1 wherein said adhesion promoter is present in an amount ranging between about 1% and about 6% by weight.

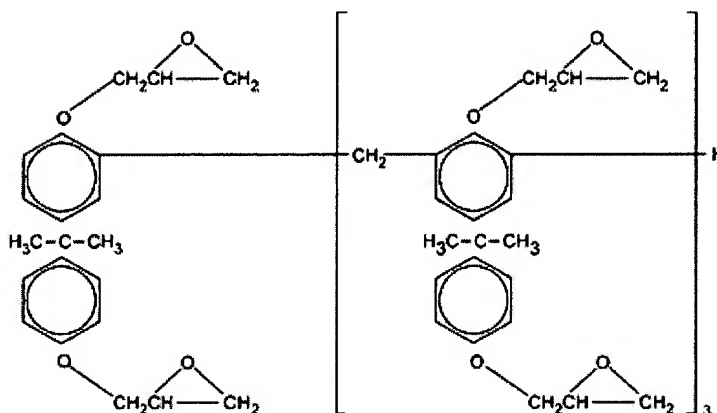
19. (currently amended) A photoresist masking material according to claim 1 wherein said adhesion promoter is present in an amount ranging between about 3% and about 4% by weight.

20. (original) A photoresist masking material according to claim 1 wherein said adhesion promoter is glycidoxypropanetrimethoxysilane.

21. (currently amended) A photoresist masking material, comprising:

- a) 50% to 75% by weight of an octafunctional epoxidized novolac resin

of the formula:



- b) 15% to 45% by weight of an organic solvent;
c) 3% to 7% by weight a photopolymerization initiator;
d) 0.5% to 3% by weight of a plasticizer selected from the group

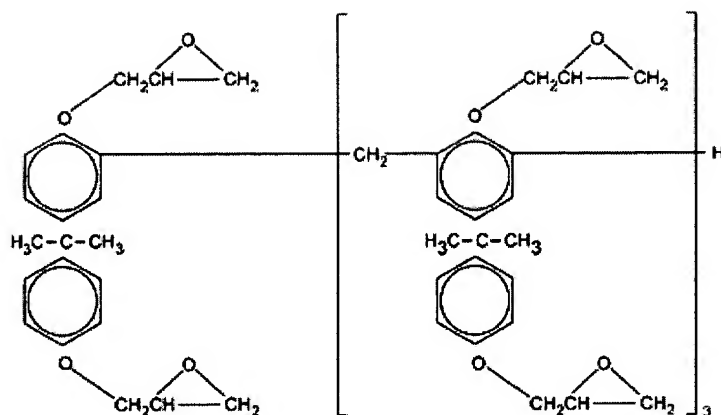
consisting of dialkylphthalates, dialkylmalonates, dialkylsebacates, dialkyladipates, and diglycidyl hexahydrophthalates; and

- e) 1% to 6% by weight of an adhesion promoter selected from the group consisting of glycidoxypropanetrimethoxysilane, mercatopropyltrimethoxysilane, and aminopropyltrimethoxysilane.

22 -26 (cancelled)

27. (new) In a method of providing a negative photoresist masking composition consisting essentially of:

- (a) an octafunctional epoxidized novolac resin is of the formula:



(b) an organic solvent; and

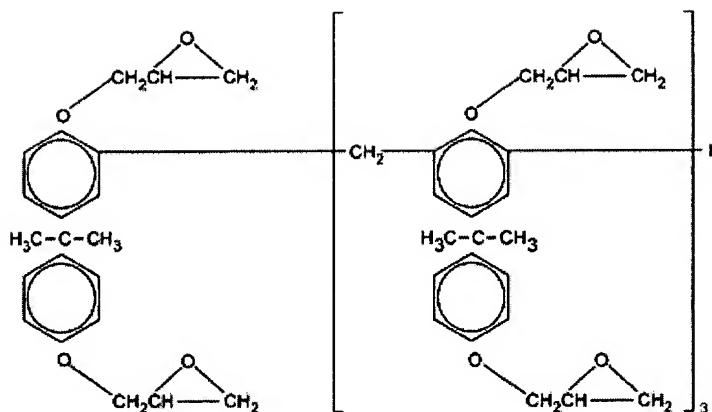
(c) a photopolymerization initiator; the improvement comprising adding to the photoresist masking composition 0.5% to 3% by weight of a member selected from the group consisting of dialkylphthalates, dialkylmalonates, dialkylsebacates, dialkyladipates, and diglycidyl hexahydrophthalates.

28. (new) The method of claim 27 wherein said member is a dialkylphthalate.

29. (new) The method of claim 27 wherein said member is dioctylphthalate.

30. (new) In a method of providing a negative photoresist masking composition consisting essentially of:

(a) an octafunctional epoxidized novolac resin is of the formula:



(b) an organic solvent; and

(c) a photopolymerization initiator; the improvement comprising adding to the photoresist masking composition 1% to 6% by weight of a member selected from the group consisting of glycidoxypropanetrimethoxysilane, mercatopropyltrimethoxysilane, and aminopropyltrimethoxysilane.

31. (new) The method of claim 30 wherein said member is glycidoxypropanetrimethoxysilane.